

N-Channel 20 V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^e	Q _g (Typ.)			
	0.028 at V _{GS} = 4.5 V	6 ^a				
20	0.042 at V _{GS} = 2.5 V	6 ^a	8.8 nC			
	0.050 at V _{GS} = 1.8 V	5.6				

SOT-23

Top View

3 D

G 1

S 2

FEATURES

- Halogen-free According to IEC 61249-2-21
 Definition
- TrenchFET[®] Power MOSFET
- 100 % $\rm R_g$ Tested
- Compliant to RoHS Directive 2002/95/EC

APPLICATIONS

- DC/DC Converters
- Load Switch for Portable Applications

Parameter	Symbol	Limit	Unit		
Drain-Source Voltage		V _{DS}	20	V	
Gate-Source Voltage		V _{GS}	± 12	V	
	T _C = 25 °C		6 ^a		
Continuous Drain Current (T. 150 °C)	T _C = 70 °C		5.1		
Continuous Drain Current ($T_J = 150 \ ^{\circ}C$)	T _A = 25 °C	I _D	5 ^{b, c}		
	T _A = 70 °C		4 ^{b, c}	A	
Pulsed Drain Current		I _{DM}	20		
Continuous Source-Drain Diode Current	T _C = 25 °C		1.75		
Continuous Source-Drain Diode Current	T _A = 25 °C	I _S	1.04 ^{b, c}		
	T _C = 25 °C		2.1		
Maximum Dawar Dissinction	T _C = 70 °C		1.3	w	
Maximum Power Dissipation	T _A = 25 °C	P _D	1.25 ^{b, c}	VV	
	T _A = 70 °C		0.8 ^{b, c}		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	<u></u>	
Soldering Recommendations (Peak Tempera		260			

THERMAL RESISTANCE RATINGS							
Parameter		Symbol	Typical	Maximum	Unit		
Maximum Junction-to-Ambient ^{b, d}	t ≤ 5 s	R _{thJA}	80	100	°C/W		
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	40	60	0/11		

Notes:

a. Package limited

b. Surface Mounted on 1" x 1" FR4 board.

c. t = 5 s.

d. Maximum under steady state conditions is 125 $^\circ\text{C/W}.$

e. Based on T_C = 25 °C.



FREE

SPECIFICATIONS $T_J = 25 \text{ °C}$, unless otherwise noted							
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static				-			
Drain-Source Breakdown Voltage	V _{DS}	V_{GS} = 0 V, I _D = 250 µA	20			V	
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I _D = 250 μA		25		- mV/°C	
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	1 <u>0</u> – 200 µ. (- 2.6			
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \ \mu A$	0.45		1.0	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 8 V$			± 100	nA	
	I _{DSS}	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}$			1	μA	
Zero Gate Voltage Drain Current		V_{DS} = 20 V, V_{GS} = 0 V, T_{J} = 70 °C			10		
On-State Drain Current ^a	I _{D(on)}	$V_{DS}{\leq}5$ V, $V_{GS}{=}4.5$ V	20			Α	
		$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 5.0 \text{ A}$		0.028	028		
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 2.5 \text{ V}, I_D = 4.7 \text{ A}$		0.042		Ω	
		$V_{GS} = 1.8 \text{ V}, \text{ I}_{D} = 4.3 \text{ A}$		0.050		-1	
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 5.0 \text{ A}$		24		S	
Dynamic ^b						<u> </u>	
Input Capacitance	-						
Output Capacitance	C _{oss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz		105		pF	
Reverse Transfer Capacitance	C _{rss}			55			
		$V_{DS} = 10 \text{ V}, \text{ V}_{GS} = 5 \text{ V}, \text{ I}_{D} = 5.0 \text{ A}$		12	18	18	
Total Gate Charge	Q _g			8.8	14	nC	
Gate-Source Charge	Q _{gs}	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 5.0 \text{ A}$		1.1			
Gate-Drain Charge	Q _{gd}			0.7			
Gate Resistance	R _g	f = 1 MHz	0.5	2.4	4.8	Ω	
Turn-On Delay Time	t _{d(on)}			8	16	- ns	
Rise Time	t _r	V_{DD} = 10 V, R _L = 2.2 Ω		17	26		
Turn-Off Delay Time	t _{d(off)}	$\text{I}_\text{D} \cong$ 4 A, V_GEN = 4.5 V, R_g = 1 Ω		31	47		
Fall Time	t _f			8	16		
Turn-On Delay Time	t _{d(on)}			5	10		
Rise Time	t _r	$V_{DD} = 10 \text{ V}, \text{ R}_{L} = 2.2 \Omega$		13	20		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 4 \text{ A}, V_{\text{GEN}} = 5 \text{ V}, \text{ R}_{\text{g}} = 1 \Omega$		21	32		
Fall Time	t _f	-		6	12		
Drain-Source Body Diode Characteristi				Ŭ	12		
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			1.75		
Pulse Diode Forward Current	I _{SM}	U			20	A	
Body Diode Voltage	V _{SD}	$I_{\rm S} = 4$ A, $V_{\rm GS} = 0$ V		0.75	1.2	v	
Body Diode Reverse Recovery Time	t _{rr}	······································		12	20	ns	
Body Diode Reverse Recovery Charge	Q _{rr}			5	10	nC	
Reverse Recovery Fall Time	t _a	$I_F = 4 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 ^\circ\text{C}$		7			
Reverse Recovery Rise Time				5		ns	
lotes:	t _b			5			

Notes:

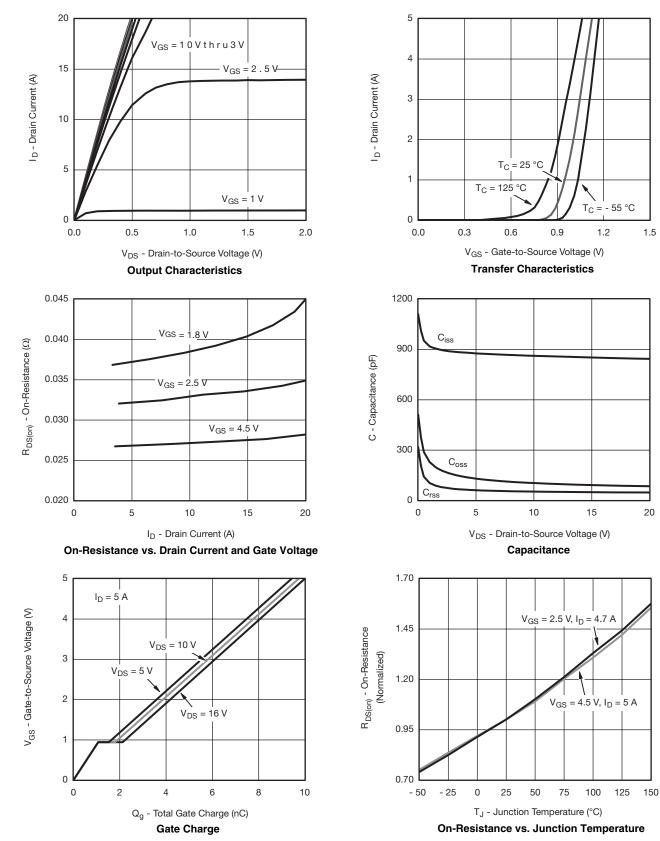
a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 % b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

emi

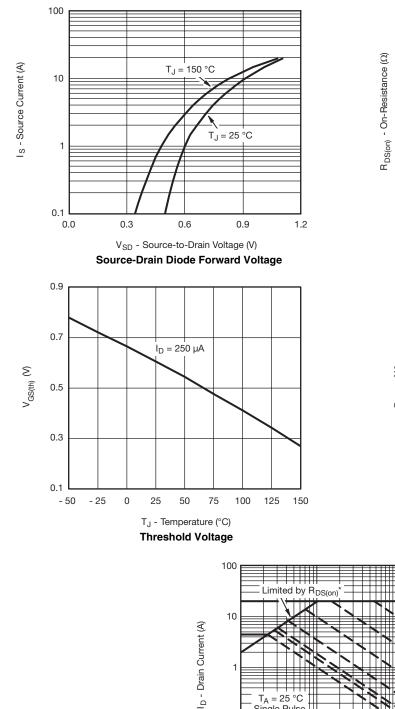
WBsemi www.VBsemi.tw

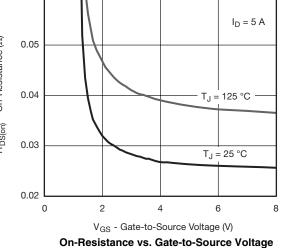
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



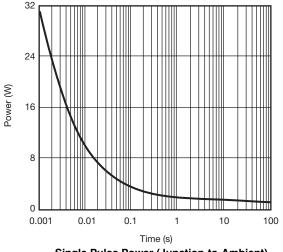


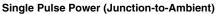
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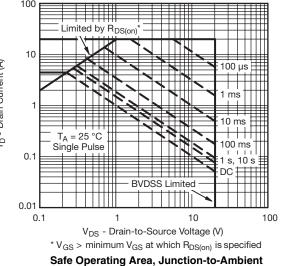




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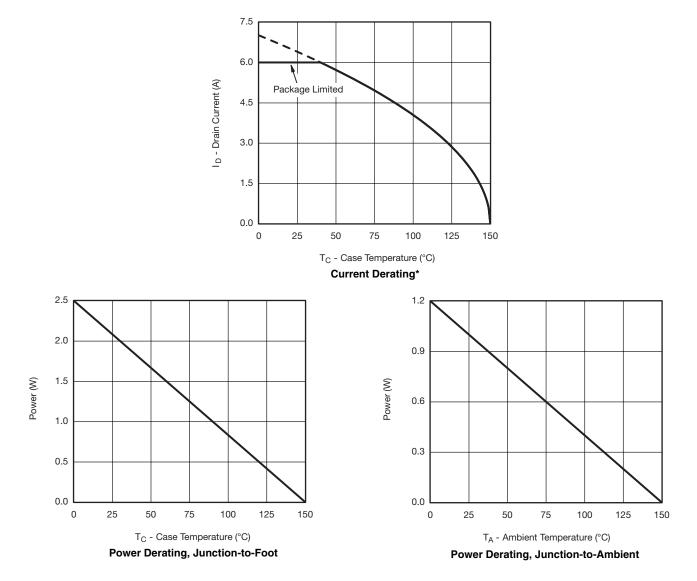








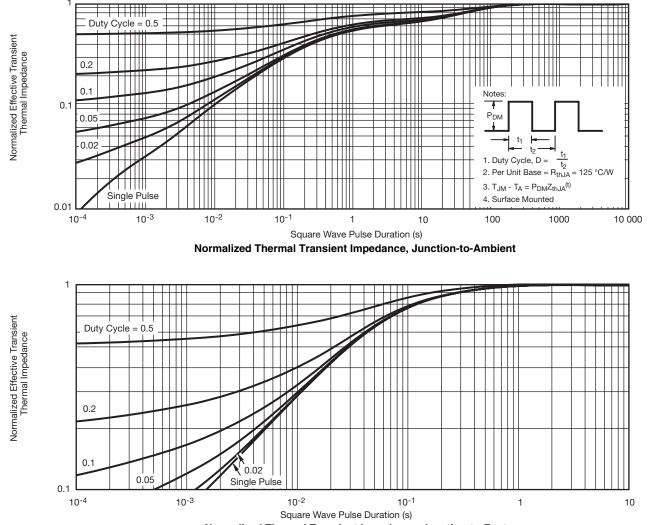
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



* The power dissipation P_D is based on $T_{J(max.)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

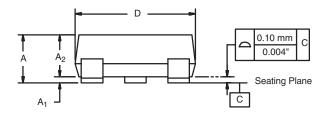


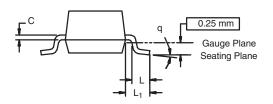
Normalized Thermal Transient Impedance, Junction-to-Foot



SOT-23 (TO-236): 3-LEAD



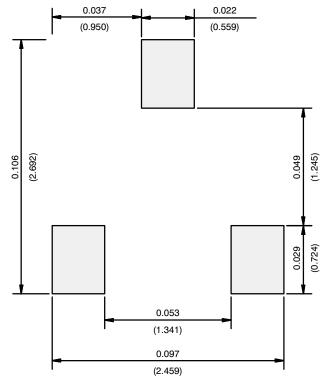




Dim	MILLIN	METERS	INCHES		
	Min	Max	Min	Мах	
Α	0.89	1.12	0.035	0.044	
A ₁	0.01	0.10	0.0004	0.004	
A ₂	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
C	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E ₁	1.20	1.40	0.047	0.055	
е	0.95 BSC		0.0374 Ref		
e ₁	1.90 BSC		0.0748 Ref		
L	0.40	0.60	0.016	0.024	
L ₁	0.64 Ref		0.025 Ref		
S	0.50 Ref		0.020 Ref		
q	3°	8°	3°	8°	
ECN: S-03946-Rev. K, 09- DWG: 5479	Jul-01	•	·		



RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads Dimensions in Inches/(mm)



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